

What is claimed is:

1. A light emitting device comprising:
a plurality of pixels provided with light emitting elements; and
5 a thin film transistor and a pixel electrode electrically connected to the thin
film transistor provided at each of the plurality of pixels,
wherein an insulating film is provided over the thin film transistor and the pixel
electrode is provided over the insulating film, and
wherein the insulating film includes an opening portion a side surface of which
10 is curved at a light emitting region.
2. The light emitting device according to claim 1, wherein the pixel electrode
comprises an oxide conductive film.
- 15 3. The light emitting device according to claim 1, wherein the insulating film is
a photosensitive resin film.
4. The light emitting device according to claim 1, wherein the opening portion
has a shape of a groove.
- 20 5. The light emitting device according to claim 1, wherein the opening portion
has a circular shape.
6. The light emitting device according to claim 1, wherein the opening portion
25 has a shape of a lattice.
7. A light emitting device comprising:
a plurality of pixels provided with light emitting elements; and
a thin film transistor and a pixel electrode electrically connected to the thin
30 film transistor provided at each of the plurality of pixels,

wherein an insulating film is provided over the thin film transistor and the pixel electrode is provided over the insulating film, and

wherein the insulating film includes an opening portion a side surface of which is curved at a light emitting region and the pixel electrode covers a side surface of the opening portion.

8. The light emitting device according to claim 7, wherein the pixel electrode comprises an oxide conductive film.

9. The light emitting device according to claim 7, wherein the insulating film is a photosensitive resin film.

10. The light emitting device according to claim 7, wherein the opening portion has a shape of a groove.

11. The light emitting device according to claim 7, wherein the opening portion has a circular shape.

12. The light emitting device according to claim 7, wherein the opening portion has a shape of a lattice.

13. A light emitting device comprising:
a plurality of pixels provided with light emitting elements; and
a thin film transistor and a pixel electrode electrically connected to the thin film transistor provided at each of the plurality of pixels;

wherein an insulating film is provided over the thin film transistor and the pixel electrode is provided over the insulating film, and

wherein the insulating film includes an opening portion a side surface of which is curved at a light emitting region and a surface of the pixel electrode includes a curved face along a shape of the opening portion.

14. The light emitting device according to claim 13, wherein the pixel electrode comprises an oxide conductive film.

5 15. The light emitting device according to claim 13, wherein the insulating film is a photosensitive resin film.

16. The light emitting device according to claim 13, wherein the opening portion has a shape of a groove.

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17. The light emitting device according to claim 13, wherein the opening portion has a circular shape.

18. The light emitting device according to claim 13, wherein the opening
15 portion has a shape of a lattice.

19. A method of manufacturing a light emitting device comprising a plurality of pixels, a thin film transistor and a pixel electrode electrically connected to the thin film transistor provided at each of the plurality of pixels, the method comprising:

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forming an insulating film;

forming an opening portion having a side surface of which is a curved in the insulating film; and

forming the pixel electrode covering the opening portion over the insulating film.

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20. The method of manufacturing a light emitting device according to claim 19, wherein the pixel electrode comprises an oxide conductive film.

21. The method of manufacturing a light emitting device according to claim 19, wherein the opening portion has a shape of a groove.

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22. The method of manufacturing a light emitting device according to claim 19, wherein the opening portion has a circular shape.

23. The method according to claim 19, wherein the opening portion has a shape
5 of a lattice.

24. A method of manufacturing a light emitting device comprising a plurality of pixels, a thin film transistor and a pixel electrode electrically connected to the thin film transistor provided at each of the plurality of pixels, the method comprising:
10 forming a photosensitive resin film;
forming an opening portion having a side surface of which is a curved in the photosensitive resin film; and
forming the pixel electrode covering the opening portion over the photosensitive resin film.

15 25. The method of manufacturing a light emitting device according to claim 24, wherein the pixel electrode comprises an oxide conductive film.

26. The method of manufacturing a light emitting device according to claim 24,
20 wherein the opening portion has a shape of a groove.

27. The method of manufacturing a light emitting device according to claim 24, wherein the opening portion has a circular shape.

25 28. The method according to claim 24, wherein the opening portion has a shape of a lattice.

29. A light emitting device comprising:
a plurality of pixels comprising a plurality of thin film transistors, a plurality of
30 pixel electrodes, and a plurality of light emitting elements; and

a insulating film formed over the plurality of thin film transistors, wherein the plurality of pixel electrodes are formed over the insulating film,

wherein the insulating film has at least one opening portion in each of the plurality of the pixels,

5 wherein the opening portion has a curved side surface at a light emitting region.

30. A light emitting device according to claim 29, wherein the pixel electrode covers a surface of the opening portion and the insulating film.

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31. A light emitting device comprising:

a plurality of pixels each of which comprises a thin film transistor, a pixel electrode electrically connected to the thin film transistor, and a light emitting element over the pixel electrode; and

15 wherein at least one island shaped insulating layer formed in each of the plurality of pixels,

wherein the pixel electrode is formed over the island shaped insulating layer,

wherein the island shaped insulating layer has at least one opening portion and the opening portion has a curved side surface.

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32. A light emitting device according to claim 31, wherein the device further comprises a data wiring, and the opening portion is formed along with the data wiring.

33. A light emitting device according to claim 31, wherein the pixel electrode
25 covers a surface of the island shaped insulating layer and the opening portion.